WSR150N04

N-Ch MOSFET

General Description

The WSR150N04 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

Product Summery

BVDSS	RDSON	ID
40V	4mΩ	150A

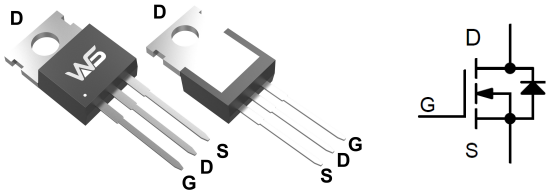
Application

- Load switch
- Battery protection
- Uninterruptible power supply

Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

TO-220AB Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	150	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	98	A
I_{DM}	Pulsed Drain Current[2]	600	A
EAS	Single Pulse Avalanche Energy[3]	350	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	180	W
T_J T_{STG}	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	0.7	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.057	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=30A	---	3	4	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.0	3.0	4.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.68	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=40V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=15A	---	40	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.8	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=10V , I_D=30A	---	80	---	nC
Q_{gs}	Gate-Source Charge		---	17	---	
Q_{gd}	Gate-Drain Charge		---	21	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=20V , V_{GS}=10V , I_D=30A , Rg=1Ω.	---	21	---	ns
T_r	Rise Time		---	32	---	
$T_{d(off)}$	Turn-Off Delay Time		---	71	---	
T_f	Fall Time		---	40	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	4950	---	pF
C_{oss}	Output Capacitance		---	530	---	
C_{rss}	Reverse Transfer Capacitance		---	321	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	150	A
I_{SM}	Pulsed Source Current[2,6]		---	---	600	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=30A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=20A ,dI/dt=100A/μs,TJ=25℃	---	27	---	nS
Q_{rr}	Reverse Recovery Charge		---	47	---	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: Tj=25℃,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25Ω

Typical Characteristics

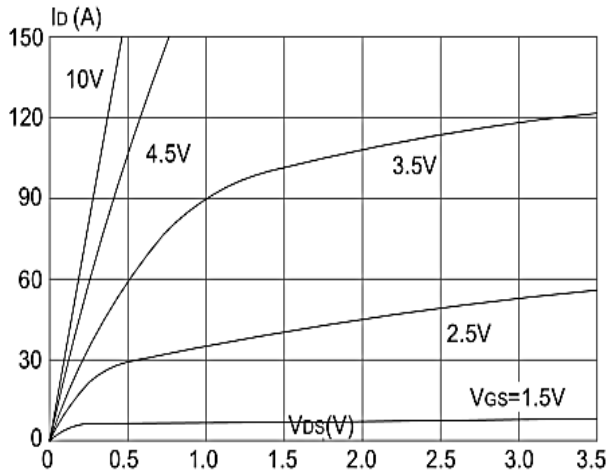


Figure1: Output Characteristics

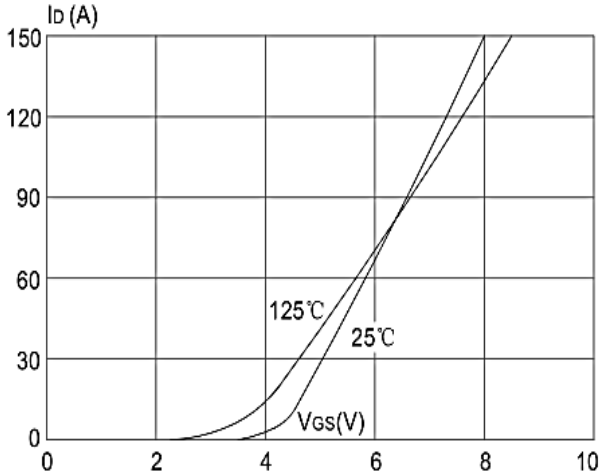


Figure 2: Typical Transfer Characteristics

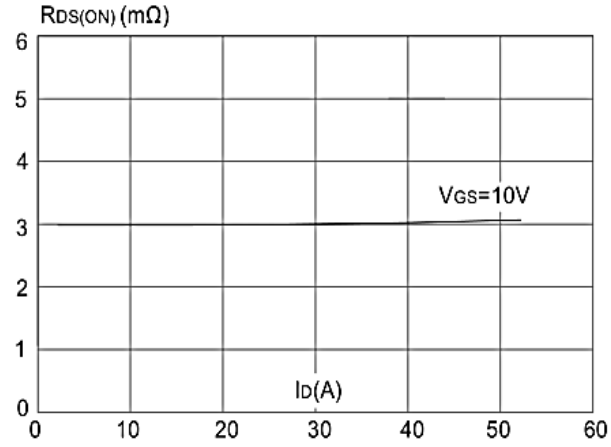


Figure 3:On-resistance vs. Drain Current

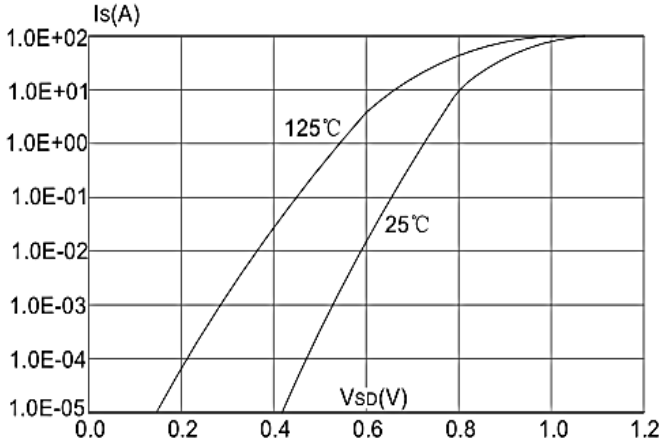


Figure 4: Body Diode Characteristics

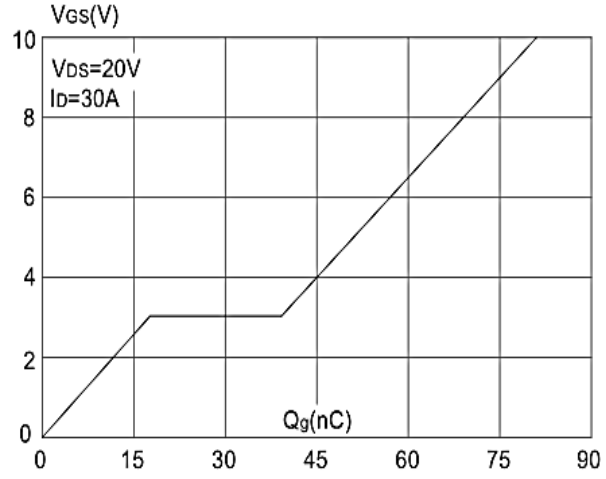


Figure 5: Gate Charge Characteristics

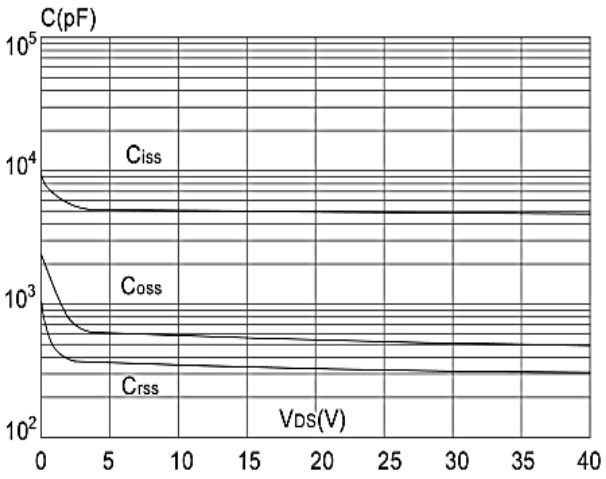


Figure 6: Capacitance Characteristics

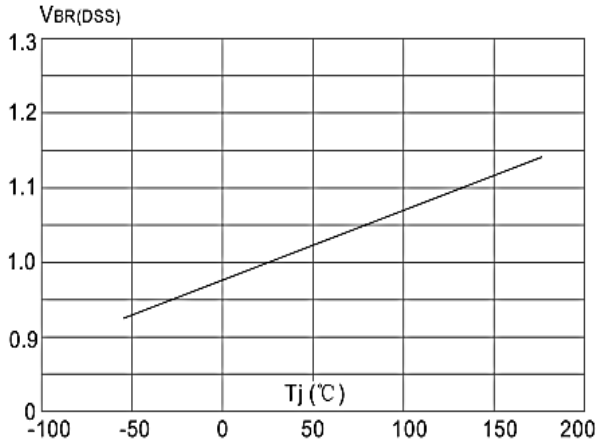


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

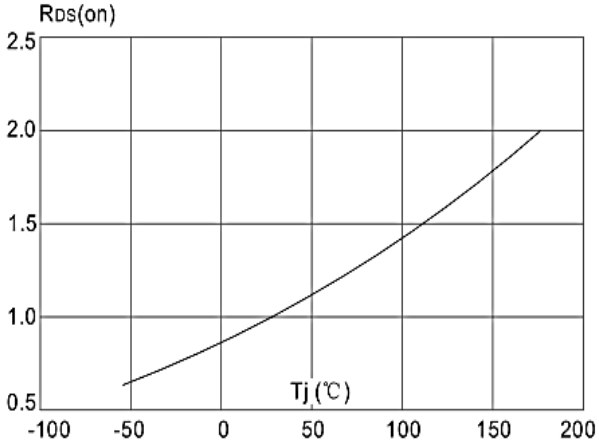


Figure 8: Normalized on Resistance vs. Junction Temperature

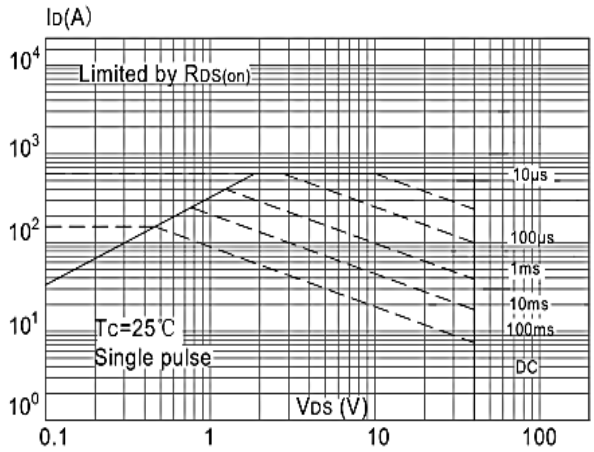


Figure 9: Maximum Safe Operating Area

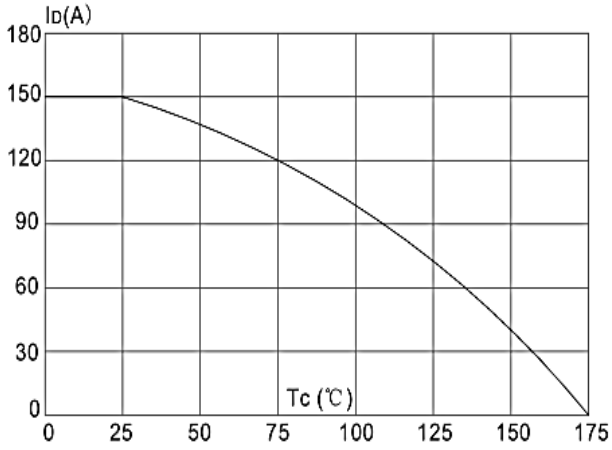


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

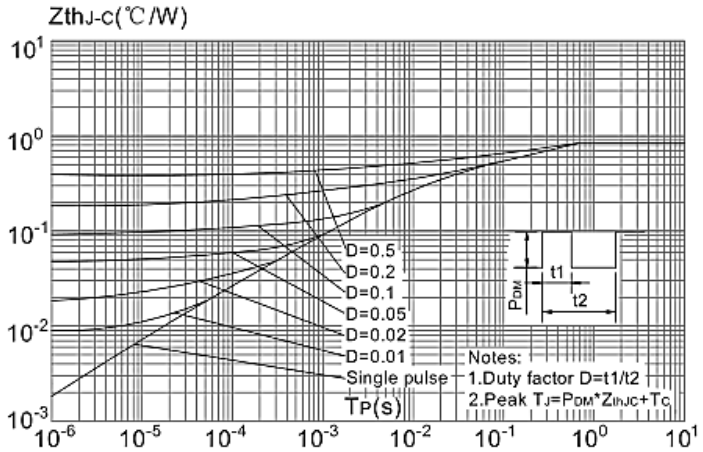


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

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